

**IN THE CLAIMS:**

**Please revise the claims to read as follows.**

1. (Previously presented) A group III nitride compound semiconductor light-emitting device, comprising:

a light-emitting layer of a multilayer quantum well structure comprising alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,

wherein said n-type clad layer is made thicker than each of said barrier layers and the thickness of said n-type clad layer is in a range of 100 Å to 500 Å, and

wherein said n-type clad layer is formed of a material substantially the same as said barrier layers, thereby providing a band gap in said n-type clad layer that is substantially the same as a band gap in said barrier layers.

2-3. (Canceled)

4. (Currently Amended) A group III nitride compound semiconductor light-emitting device according to claim 1, further comprising an intermediate layer which is provided so as to be in contact with a face of said n-type clad layer opposite to said light-emitting layer, said intermediate layer being devoid of aluminum.

5. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said intermediate layer is made of  $\text{In}_x\text{Ga}_{1-x}\text{N}$ , where  $(0 < x < 1)$ .

6. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said intermediate layer is made of  $\text{In}_x\text{Ga}_{1-x}\text{N}$ , where  $(0.01 \leq x \leq 0.05)$ .

7. (Previously presented) The group III nitride compound semiconductor light-emitting device of claim 1, wherein said n-type clad layer and said barrier layers are formed of GaN.

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8. (Previously presented) The semiconductor light-emitting device of claim 1, wherein a thickness of said well layer is approximately 30 Å and a thickness of said barrier layer is approximately 70 Å.

9. (Previously presented) The semiconductor light-emitting device of claim 1, further comprising:

a cap layer formed on said light-emitting layer, said cap layer being formed of a material substantially the same as said barrier layers; and

a p-type clad layer formed on and contacting said cap layer.

10. (Previously presented) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 180 Å to 500 Å, and a light emitted comprises green light in a wavelength range of approximately 510 nm to 530 nm.

11. (Previously presented) The semiconductor light-emitting device of claim 10, wherein said thickness of said p-type clad layer is in a range of approximately 240 Å to 360 Å.

12. (Previously presented) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 90 Å to 390 Å, and a light emitted comprises blue light in a wavelength range of approximately 460 nm to 475 nm.

13. (Previously presented) The semiconductor light-emitting device of claim 12, wherein said thickness of said p-type clad layer is in a range of approximately 120 Å to 300 Å.

14. (Previously presented) The semiconductor light-emitting device of claim 9, wherein said p-type clad layer comprises p-type doped  $\text{Al}_x\text{Ga}_{1-x}\text{N}$ , where x ranges from approximately 0.10 to 0.14.

15. (Previously presented) A group III nitride compound semiconductor light-emitting device, comprising:

a light-emitting layer of a multilayer quantum well structure comprising alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,

wherein said n-type clad layer is made thicker than each of said barrier layers, said n-type clad layer is formed of a material substantially the same as said barrier layers, said material thereby providing a band gap in said n-type clad layer that is substantially the same as a band gap in said barrier layers.

16. (Previously presented) The group III nitride compound semiconductor light-emitting device of claim 15, wherein said barrier layers comprise GaN.

FI 17. (Previously presented) The group III nitride compound semiconductor light-emitting device of claim 15, further comprising:

a cap layer in contact with said light-emitting layer on a side of said light-emitting layer opposite to that contacting said n-type clad layer, said cap layer being formed of a material substantially the same as said barrier layers.

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### III. Formal matters and Conclusion

In view of the foregoing, Applicant submits that claims 1 and 4-17, all the claims presently pending in the application, are patentably distinct over the prior art of record and are in condition for allowance. The Examiner is respectfully requested to pass the above application to issue at the earliest possible time.

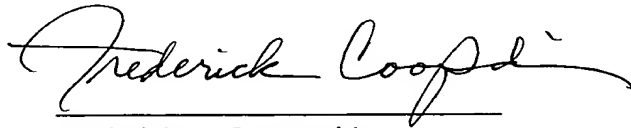
Should the Examiner find the application to be other than in condition for allowance, the Examiner is requested to contact the undersigned at the local telephone number listed below to discuss any other changes deemed necessary in a telephonic or personal interview.

The Commissioner is hereby authorized to charge any deficiency in fees or to credit any overpayment in fees to Attorney's Deposit Account No. 50-0481.

Date: \_\_\_\_\_

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Respectfully Submitted,



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